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NTE216 Silicon NPN Transistor High Speed Switch, Core Driver

Absolute Maximum Ratings:

Collector-Base Voltage, V_{CB0}	80V
Collector-Emitter Voltage, V_{CEO}	50V
Emitter-Base Voltage, V_{EBO}	6V
Collector Current, I_C	1.5A
Power Dissipation ($T_A = +25^\circ\text{C}$), P_D	1.2W
Maximum Operating Temperature, T_{opr}	+150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 60V$	-	-	1.7	μA
DC Current Gain	h_{FE}	$I_C = 10mA, V_{CE} = 1V$	30	-	-	
		$I_C = 150mA, V_{CE} = 1V$	60	-	150	
		$I_C = 300mA, V_{CE} = 1V$	40	-	-	
		$I_C = 500mA, V_{CE} = 1V$	35	-	-	
		$I_C = 800mA, V_{CE} = 2V$	20	-	-	
		$I_C = 1A, V_{CE} = 5V$	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA$	-	-	0.25	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10mA$	-	-	0.76	V
Capacitance	C_{ob}		-	-	10	pF
Turn-Off Time	t_{off}	$V_{CC} = 30V, I_C = 500mA,$ $I_{B1} = I_{B2} = 50mA$	-	-	60	ns

